

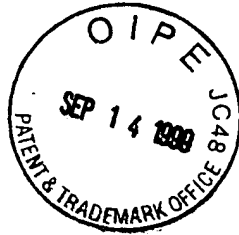
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of
Masayuki Yasuda

Serial No.: 09/019,087

Filed: 02/05/98

Title: Manufacturing Method of Semiconductor IC Device



Docket No.: TIJ-24816

Art Unit: 1765

Examiner: Perez Ramos, V.

#6/B
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9/29/99

AMENDMENT UNDER 37 CFR 1.115

Assistant Commissioner for Patents
Box Non-fee Amendments
Washington, D. C. 20231

MAILING CERTIFICATE UNDER 37 C.F.R. §1.8(A)
I hereby certify that this correspondence is being deposited with
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D.C. 20231.

William B. Kempler, Reg. No. 28,228

10 September, 1999
Date

Sir:

In response to the Office Action dated May 12, 1999 in the above-identified patent application, please make the following amendments. They are respectfully submitted as a full and complete response to that Action.

IN THE CLAIMS:

Please amend Claims 1-3 as follows:

1. (Twice Amended) A manufacturing method of a semiconductor IC device, comprising the following steps:
- forming an insulating film on a semiconductor substrate or SOI substrate;
 - forming a first mask film on the insulating film;
 - forming a resist film on the first mask film, the resist film being used as an etching mask to form an opening on the first mask film, followed by the formation of trenches on the insulating film exposed from the opening;

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